

PTO/SB/08A (08-03)

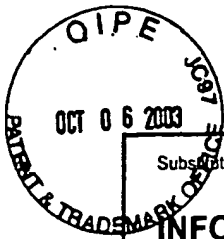
<b>Substitute for form 1449/PTO</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete if Known</b>			
		Application Number	10/660,813		
		Filing Date	September 12, 2003		
		First Named Inventor	Mungekar, Hemant P.		
		Art Unit			
		Examiner Name	Not yet assigned		
Sheet	1	of	3	Attorney Docket Number	A8067/T51700

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	US-4,690,746	09-01-1987	McInerney et al.	
	A2	US-4,737,379	04-12-1988	Hudgens et al.	
	A3	US-4,835,005	05-30-1989	Hirooka et al.	
	A4	US-4,872,947	10-10-1989	Wang et al.	
	A5	US-4,890,575	01-02-1990	Ito et al.	
	A6	US-4,892,753	01-09-1990	Wang et al.	
	A7	US-4,960,488	10-02-1990	Law et al.	
	A8	US-5,000,113	03-19-1991	Wang et al.	
	A9	US-5,089,442	02-18-1992	Olmer	
	A10	US-5,156,881	10-20-1992	Okano et al.	
	A11	US-5,271,972	12-21-1993	Kwok et al.	
	A12	US-5,275,977	01-04-1994	Otsubo et al.	
	A13	US-5,279,865	01-18-1994	Chebi et al.	
	A14	US-5,302,233	04-12-1994	Kim et al.	
	A15	US-5,319,247	06-07-1994	Matsuura	
	A16	US-5,362,526	11-08-1994	Wang et al.	
	A17	US-5,416,048	05-16-1995	Blalock et al.	
	A18	US-5,468,342	11-21-1995	Nulty et al.	
	A19	US-5,571,576	11-05-1996	Qian et al.	
	A20	US-5,599,740	02-04-1997	Jang et al.	
	A21	US-5,624,582	04-29-1997	Cain	
	A22	US-5,645,645	07-08-1997	Zhang et al.	
	A23	US-5,679,606	10-21-1997	Wang et al.	
	A24	US-5,712,185	01-27-1998	Tsai et al.	
	A25	US-5,719,085	02-17-1998	Moon et al.	
	A26	US-5,804,259	09-08-1998	Robles	
	A27	US-5,850,105	12-15-1998	Dawson et al.	
	A28	US-5,858,876	01-12-1999	Chew	
	A29	US-5,872,052	02-16-1999	Iyer	
	A30	US-5,872,058	02-16-1999	Van Cleemput et al.	
	A31	US-5,910,342	06-08-1999	Hirooka et al.	
	A32	US-5,913,140	06-15-1999	Roche et al.	
	A33	US-5,915,190	06-22-1999	Pirkle	
	A34	US-5,937,323	08-10-1999	Orczyk et al.	
	A35	US-5,953,635	09-14-1999	Andideh	
	A36	US-5,968,610	10-19-1999	Liu et al.	
	A37	US-5,976,327	11-02-1999	Tanaka	
	A38	US-5,990,013	11-23-1999	Berenguer et al.	
	A39	US-5,990,000	11-23-1999	Hong et al.	
	A40	US-6,013,191	01-11-2000	Nasser-Faili et al.	
	A41	US-6,013,584	01-11-2000	M'Saad	

Examiner Signature		Date Considered	9/16/05
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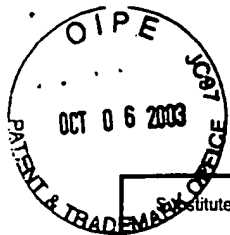
Substitute for form 1449A/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	10/660,813
		Filing Date	September 12, 2003
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		Art Unit	
		Examiner Name	Not yet assigned
Sheet <b>2</b>	of <b>3</b>	Attorney Docket Number	A8067/T51700

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		Number Kind Code <sup>2</sup> (if known)			
	A42	US-6,030,881	02-29-2000	Papasoulotis et al.	
	A43	US-6,037,018	03-14-2000	Jang et al.	
	A44	US-6,039,851	03-21-2000	Iyer	
	A45	US-6,059,643	05-09-2000	Hu et al.	
	A46	US-6,136,685	10-24-2000	Narwankar et al.	
	A47	US-6,167,834 B1	01-02-2001	Wang et al.	
	A48	US-6,170,428 B1	01-09-2001	Redeker et al.	
	A49	US-6,182,602 B1	02-06-2001	Redeker et al.	
	A50	US-6,189,483 B1	02-20-2001	Ishikawa et al.	
	A51	US-6,191,026 B1	02-20-2001	Rana et al.	
	A52	US-6,203,863 B1	03-20-2001	Liu et al.	
	A53	US-6,194,038 B1	02-27-2001	Rossman	
	A54	US-6,197,705 B1	03-06-2001	Vassiliev	
	A55	US-6,217,658 B1	04-17-2001	Orczyk et al.	
	A56	US-6,228,751 B1	05-08-2001	Yamazaki et al.	
	A57	US-6,313,010 B1	11-06-2001	Nag et al.	
	A58	US-6,335,288 B1	01-01-2002	Kwan et al.	
	A59	US-6,395,150 B1	05-28-2002	Van Cleemput et al.	
	A60	US 2002-0187655 A1	12-12-2002	Tan	
	A61	US-6,503,843 B1	01-07-2003	Xia et al.	
	A62	US-6,596,654 B1	07-22-2003	Bayman et al.	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
	B1	JP	7-161703	A	06-23-1995		Abstract only	<input type="checkbox"/>
	B2	JP	2058836	A	02-28-1990		Abstract only	<input type="checkbox"/>
	B3	GB	2 267 291		12-01-1993			<input type="checkbox"/>

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
<i>per</i>	C1	ABRAHAM, "Reactive Facet Tapering of Plasma Oxide For Multilevel Interconnect Applications," VMIC Conference, pgs. 115-121 (1987).	
	C2	LEE et al., "Dielectric Planarization Techniques For Narrow Pitch Multilevel Interconnects," VMIC Conference, pgs. 85-92 (1987).	
	C3	MUSAKA, "Single Step Gap Filling Technology fo Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O <sub>2</sub> Chemical Vapor Deposition System," International Conference on Solid State Devices and Materials pgs. 510-512, held in Japan, (1993).	
	C4	NALWA, H.S., Handbook of Low and High Dielectric Constant Materials and Their Applications, vol. 1, page 66 (1999).	
	C5	NGUYEN, s.v., "High-Density Plasma Chemical Vapor Deposition of Silicon-Based Dielectric Films for Integrated Circuits," Journal of Research and Development, vol. 43, 1/2 (1999).	
	C6	QIAN et al., "High Density Plasma Deposition and Deep Submicron Gap Fill with Low Dielectric Constant SiOF Films," DUMIC Conference, pgs. 50-56, held in California (1995).	
<i>u</i>	C7	VASSILIEUV et al., "Trends in void-free pre-metal CVD dielectrics," <u>Solid State Technology</u> , 2001, pgs. 129-136, www.solid-state.com.	

Examiner Signature	<i>[Signature]</i>	Date Considered	9/16/05
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